

UTC UNISONIC TECHNOLOGIES CO., LTD

UT2311

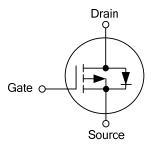
Power MOSFET

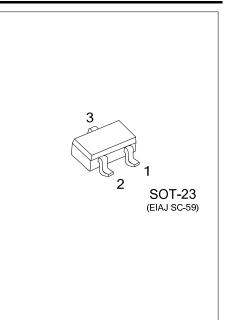
-4A, -20V P-CHANNEL **ENHANCEMENT MODE MOSFET**

FEATURES

- * Extremely low on-resistance due to high density cell
- * Perfect thermal performance and electrical capability with advanced technology of trench process

SYMBOL





ORDERING INFORMATION

Ordering Number		Daakaga	Pin Assignment			Docking	
		Package	1	2	3	Packing	
UT2311G-AE3-R		SOT-23	S	G	D	Tape Reel	
Note: Pin Assignment: G: Gate	D: Drain S: Source						
	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape R (2) AE3: SOT (3) G: Haloger	-23	nd Lea	d Free		

MARKING



■ **ABSOLUTE MAXIMUM RATINGS** (T_A = 25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current	I _D	-4	А
Pulsed Drain Current	I _{DM}	-20	А
Power Dissipation (T _A =25°C) (Note 2)	PD	1.25	W
Junction Temperature	TJ	+150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Surface mounted on 1 in $_2$ copper pad of FR4 board.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (PCB mounted)	θ _{JA}	100	°C/W

Note: Surface Mounted on FR4 board t \leq 5 sec.

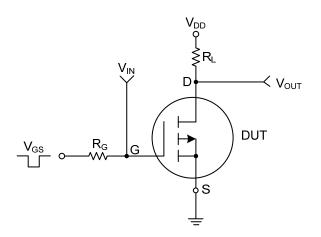
■ ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise specified)

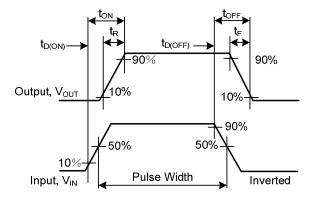
P						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V, I _D =-250µA	-20			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-16V,V _{GS} =0V			-1.0	μA
Gate-Source Leakage Current	I _{GSS}	V_{GS} =±8V, V_{DS} =0V			±100	nA
ON CHARACTERISTICS			-			
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-250µA	-0.45			V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4.0 A		45	55	mΩ
		V _{GS} =-2.5V, I _D =-2.5 A		75	85	mΩ
On-State Drain Current	I _{D(ON)}	V _{DS} ≥ -10V, V _{GS} =-4.5V	-6			А
DYNAMIC PARAMETERS ^b						
Input Capacitance	CISS			970		рF
Output Capacitance	Coss	V _{DS} =-6V, V _{GS} =0 V, f =1.0MHz		485		рF
Reverse Transfer Capacitance	C _{RSS}			160		рF
SWITCHING PARAMETERS ^b						
Turn-ON Delay Time	t _{D(ON)}			18		ns
Turn-ON Rise Time	t _R	V _{DD} =-4V, V _{GEN} =-4.5V, I _D =-1A		45		ns
Turn-OFF Delay Time	t _{D(OFF)}	R_L =4Ω, R_G =6Ω		95		ns
Turn-OFF Fall-Time	t _F			65		ns
Total Gate Charge	Q_{G}			8.5	12	nC
Gate Source Charge	Q_{GS}	V_{GS} =-4.5V, V_{DS} =-6V, I_{D} =-4.0A		1.5		nC
Gate Drain Charge	Q_{GD}			2.1		nC
SOURCE- DRAIN DIODE RATINGS AND	CHARAC	TERISTICS				
Drain-Source Diode Forward Voltage	V_{SD}	V _{GS} =0 V, I _S =-1.6A,		-0.8	-1.2	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				-1.6	A

Note: Pulse test; pulse width \leq 300µs, duty cycle \leq 2%.



TEST CIRCUITS AND WAVEFORMS



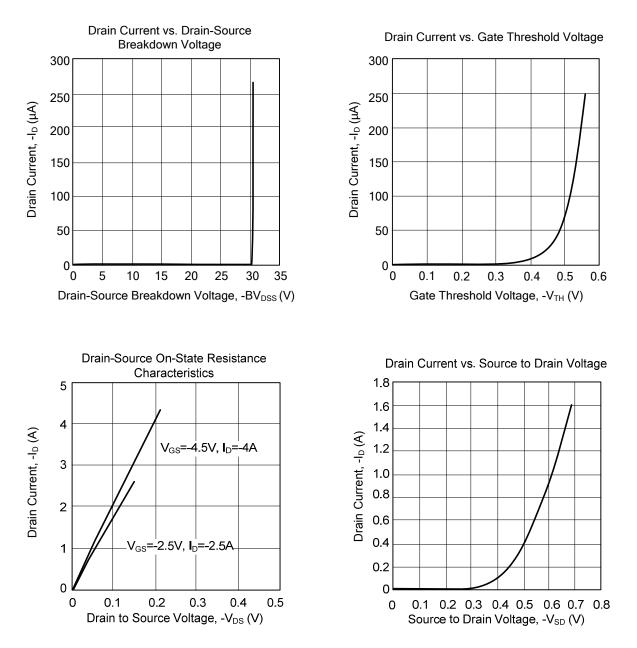


Switching Test Circuit

Switching Waveforms



TYPICAL CHARACTERISTICS



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